

# Phase Control Thyristors (Hockey PUK Version), 350 A



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PRIMARY CHARACTERISTICS				
I <sub>T(AV)</sub>	350 A			
V <sub>DRM</sub> /V <sub>RRM</sub>	400 V, 800 V, 1200 V, 1600 V, 1800 V, 2000 V			
V <sub>TM</sub>	1.96 V			
I <sub>GT</sub>	90 mA			
$T_J$	-40 °C to +125 °C			
Package	A-PUK (TO-200AB)			
Circuit configuration	Single SCR			

#### **FEATURES**

- · Center amplifying gate
- Metal case with ceramic insulator
- International standard case A-PUK (TO-200AB)



- Designed and qualified for industrial level
- Material categorization: for definitions of compliance please see <a href="https://www.vishay.com/doc?99912"><u>www.vishay.com/doc?99912</u></a>

#### **TYPICAL APPLICATIONS**

- DC motor controls
- Controlled DC power supplies
- AC controllers

MAJOR RATINGS AND CHARACTERISTICS					
PARAMETER	TEST CONDITIONS	VALUES	UNITS		
		350	A		
I <sub>T(AV)</sub>	T <sub>hs</sub>	55	°C		
1		660	A		
I <sub>T(RMS)</sub>	T <sub>hs</sub>	25	°C		
I <sub>TSM</sub>	50 Hz	5000	Δ.		
	60 Hz	5230	A		
l <sup>2</sup> t	50 Hz	125	kA <sup>2</sup> s		
	60 Hz	114	KA-S		
V <sub>DRM</sub> /V <sub>RRM</sub>		400 to 2000	V		
tq	Typical	100	μs		
T <sub>J</sub>		-40 to +125	°C		

#### **ELECTRICAL SPECIFICATIONS**

VOLTAGE RATINGS								
TYPE NUMBER	VOLTAGE CODE	V <sub>DRM</sub> /V <sub>RRM</sub> , MAXIMUM REPETITIVE PEAK AND OFF-STATE VOLTAGE V	V <sub>RSM</sub> , MAXIMUM NON-REPETITIVE PEAK VOLTAGE V	$\begin{aligned} I_{DRM}/I_{RRM} & \text{MAXIMUM} \\ \text{AT T}_{J} &= \text{T}_{J} & \text{MAXIMUM} \\ & \text{mA} \end{aligned}$				
	04	400	500					
	08	800	900					
VS-ST180CC	12	1200	1300	30				
V3-311600C	16	1600	1700	30				
	18	1800	1900					
	20	2000	2100					

Revision: 27-Sep-17 **1** Document Number: 94396



PARAMETER	SYMBOL		TEST CONDITIONS				
Maximum average on-state current		180° condu	ction, half sine v	wave	350 (140)	Α	
at heatsink temperature	I <sub>T(AV)</sub>	double side	(single side) co	oled	55 (85)	°C	
Maximum RMS on-state current	I <sub>T(RMS)</sub>	DC at 25 °C	heatsink tempe	erature double side cooled	660		
		t = 10 ms	No voltage		5000		
Maximum peak, one-cycle		t = 8.3 ms	reapplied	reapplied		Α	
non-repetitive surge current	I <sub>TSM</sub>	t = 10 ms	100 % V <sub>RRM</sub>		4200		
		t = 8.3 ms	reapplied Sinusoidal half wave,	Sinusoidal half wave,	4400		
		t = 10 ms	No voltage	initial $T_J = T_J$ maximum	125	- kA <sup>2</sup> s	
NA	I <sup>2</sup> t	t = 8.3 ms			114		
Maximum I <sup>2</sup> t for fusing	1-1	t = 10 ms			88		
		t = 8.3 ms	reapplied		81		
Maximum I <sup>2</sup> √t for fusing	I <sup>2</sup> √t	t = 0.1 to 10	t = 0.1 to 10 ms, no voltage reapplied			kA²√s	
Low level value of threshold voltage	V <sub>T(TO)1</sub>	(16.7 % x π	$x I_{T(AV)} < I < \pi x$	$I_{T(AV)}$ ), $T_J = T_J$ maximum	1.08	V	
High level value of threshold voltage	V <sub>T(TO)2</sub>	$(I > \pi \times I_{T(AV)}), T_J = T_J \text{ maximum}$		1.14	]		
Low level value of on-state slope resistance	r <sub>t1</sub>	(16.7 % x $\pi$ x $I_{T(AV)}$ < I < $\pi$ x $I_{T(AV)}$ ), $T_J = T_J$ maximum		1.18	mΩ		
High level value of on-state slope resistance	r <sub>t2</sub>	$(I > \pi \times I_{T(AV)}), T_J = T_J \text{ maximum}$		1.14	11122		
Maximum on-state voltage	$V_{TM}$	$I_{pk} = 750 \text{ A}, T_J = T_J \text{ maximum, } t_p = 10 \text{ ms sine pulse}$		1.96	V		
Maximum holding current	I <sub>H</sub>	T 25 °C	T 05 00 and a cal 40 V calatic lead		600	mA	
Maximum (typical) latching current	IL	T <sub>J</sub> = 25 °C, anode supply 12 V resistive load		1000 (300)	IIIA		

SWITCHING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum non-repetitive rate of rise of turned-on current	dl/dt	Gate drive 20 V, 20 $\Omega$ , $t_r \le 1~\mu s$ $T_J = T_J$ maximum, anode voltage $\le 80~\%~V_{DRM}$	1000	A/µs
Typical delay time	t <sub>d</sub>	Gate current 1 A, $dl_g/dt = 1 A/\mu s$ $V_d = 0.67 \% V_{DRM}, T_J = 25 °C$	1.0	
Typical turn-off time	t <sub>q</sub>	$I_{TM}$ = 300 A, $T_J$ = $T_J$ maximum, dl/dt = 20 A/μs, $V_R$ = 50 V, dV/dt = 20 V/μs, gate 0 V 100 $\Omega$ , $t_p$ = 500 μs	100	μs

BLOCKING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum critical rate of rise of off-state voltage	dV/dt	T <sub>J</sub> = T <sub>J</sub> maximum linear to 80 % rated V <sub>DRM</sub>	500	V/µs
Maximum peak reverse and off-state leakage current	I <sub>RRM</sub> , I <sub>DRM</sub>	$T_J = T_J$ maximum, rated $V_{DRM}/V_{RRM}$ applied	30	mA



TRIGGERING						
PARAMETER	SYMBOL	TEST CONDITIONS		VALUES		UNIT
PANAMETEN	STWIBOL	'	TEST CONDITIONS		max.	S
Maximum peak gate power	$P_{GM}$	$T_J = T_J$ maximum,	$t_p \leq 5 \; ms$	1	0	W
Maximum average gate power	P <sub>G(AV)</sub>	$T_J = T_J$ maximum,	f = 50 Hz, d% = 50	2	.0	V V
Maximum peak positive gate current	I <sub>GM</sub>			3	.0	Α
Maximum peak positive gate voltage	+ V <sub>GM</sub>	$T_J = T_J$ maximum, $t_p \le 5$ ms		20		V
Maximum peak negative gate voltage	- V <sub>GM</sub>	·			5.0	
		T <sub>J</sub> = - 40 °C		180	-	mA
DC gate current required to trigger	$I_{GT}$	T <sub>J</sub> = 25 °C	Maximum required gate trigger/	90	150	
		T <sub>J</sub> = 125 °C	current/voltage are the lowest value	40	-	İ
		T <sub>J</sub> = - 40 °C	which will trigger all units 12 V	2.9	-	
DC gate voltage required to trigger	$V_{GT}$	T <sub>J</sub> = 25 °C anode to cathode applied	anode to cathode applied	1.8	3.0	V
		T <sub>J</sub> = 125 °C		1.2	-	
DC gate current not to trigger	I <sub>GD</sub>		Maximum gate current/voltage not	1	0	mA
DC gate voltage not to trigger	V <sub>GD</sub>	$T_J = T_J$ maximum which will not trigger any unit rated $V_{DRM}$ anode to cathode applied		0.25		V

THERMAL AND MECHANICAL SPECIFICATIONS					
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNIT S	
Maximum operating junction temperature range	TJ		-40 to 125	°C	
Maximum storage temperature range	T <sub>Stg</sub>		-40 to 150		
Maximum thermal resistance,	В	DC operation single side cooled	0.17		
junction to heatsink	R <sub>thJ-hs</sub>	DC operation double side cooled	0.08	K/W	
Maximum thermal resistance,	D	DC operation single side cooled	0.033	r\/vv	
case to heatsink	R <sub>thC-hs</sub>	DC operation double side cooled	0.017		
Mounting force, ± 10 %			4900 (500)	N (kg)	
Approximate weight			50	g	
Case style		See dimensions - link at the end of datasheet	A-PUK (TO-2	200AB)	

△R <sub>thJC</sub> CONDUCTION								
SINUSOIDAL CONDUCTION ANGLE CONDUCTION			RECTANGULAR CONDUCTION		TEST CONDITIONS	UNITS		
	SINGLE SIDE	DOUBLE SIDE	SINGLE SIDE	DOUBLE SIDE				
180°	0.015	0.015	0.011	0.011				
120°	0.018	0.019	0.019	0.019	$T_J = T_J$ maximum			
90°	0.024	0.024	0.026	0.026		K/W		
60°	0.035	0.035	0.036	0.037				
30°	0.060	0.060	0.060	0.061				

#### Note

• The table above shows the increment of thermal resistance R<sub>thJC</sub> when devices operate at different conduction angles than DC



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## Vishay Semiconductors

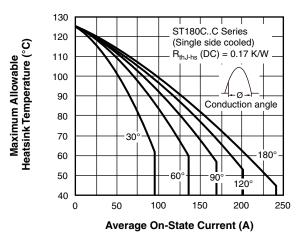
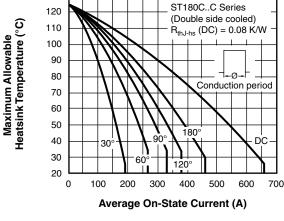


Fig. 1 - Current Ratings Characteristics



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Fig. 4 - Current Ratings Characteristics

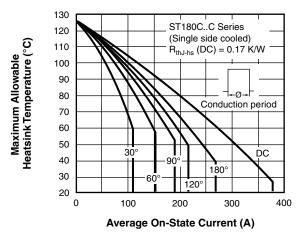


Fig. 2 - Current Ratings Characteristics

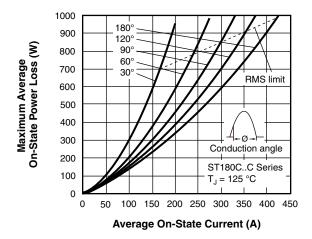


Fig. 5 - On-State Power Loss Characteristics

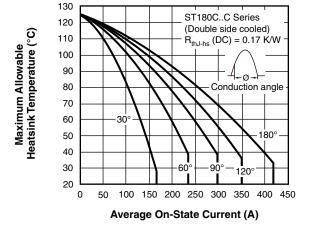


Fig. 3 - Current Ratings Characteristics

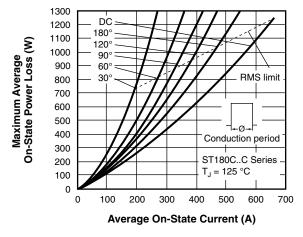


Fig. 6 - On-State Power Loss Characteristics

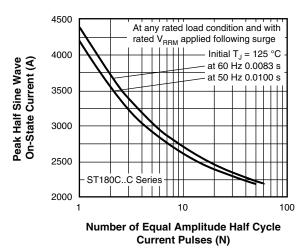


Fig. 7 - Maximum Non-Repetitive Surge Current Single and Double Side Cooled

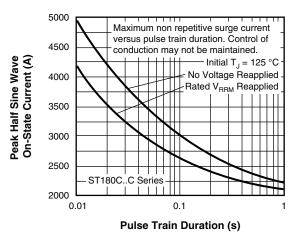


Fig. 8 - Maximum Non-Repetitive Surge Current Single and Double Side Cooled

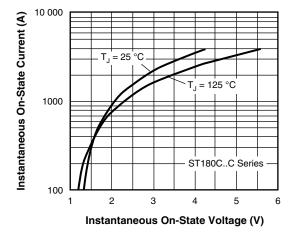


Fig. 9 - On-State Voltage Drop Characteristics

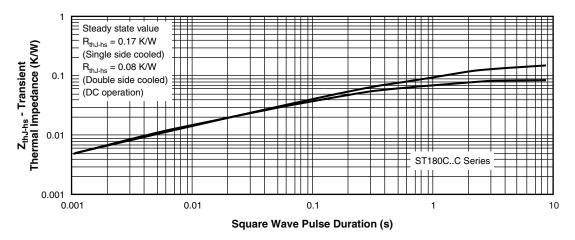


Fig. 10 - Thermal Impedance  $Z_{\text{thJ-hs}}$  Characteristics

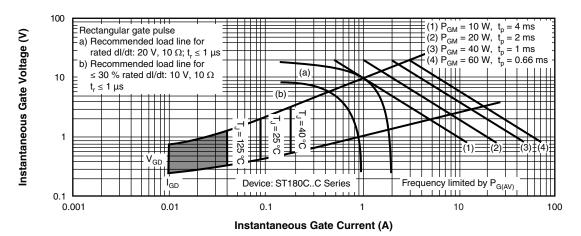
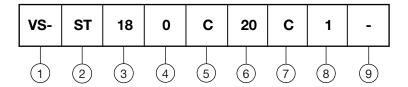


Fig. 11 - Gate Characteristics

#### **ORDERING INFORMATION TABLE**

Device code



1 - Vishay Semiconductors product

2 - Thyristor

3 - Essential part number

4 - 0 = converter grade

**5** - C = ceramic PUK

Voltage code x 100 = V<sub>RRM</sub> (see Voltage Ratings table)

7 - C = PUK case A-PUK (TO-200AB)

0 = eyelet terminals (gate and auxiliary cathode unsoldered leads)

1 = fast-on terminals (gate and auxiliary cathode unsoldered leads)

2 = eyelet terminals (gate and auxiliary cathode soldered leads)

3 = fast-on terminals (gate and auxiliary cathode soldered leads)

9 - Critical dV/dt: • None = 500 V/µs (standard selection)

• L = 1000 V/µs (special selection)

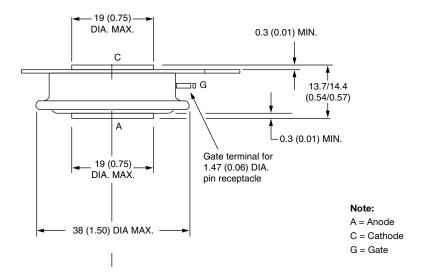
LINKS TO RELATED DOCUMENTS				
Dimensions	www.vishay.com/doc?95074			

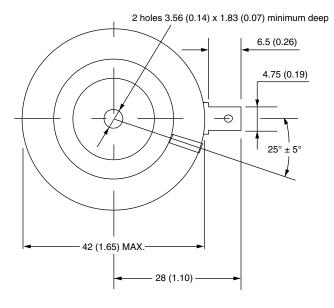


# **A-PUK (TO-200AB)**

#### **DIMENSIONS** in millimeters (inches)

Anode to gate Creepage distance: 7.62 (0.30) minimum Strike distance: 7.12 (0.28) minimum





Quote between upper and lower pole pieces has to be considered after application of mounting force (see thermal and mechanical specification)



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